

IN THE ABSTRACT:

The following Abstract will replace all prior versions of itself in the application.

--ABSTRACT

A semiconductor light emitting device including a transparent compound semiconductor substrate whose lattice constant is inconsistent with the compound semiconductor emitting the light and exhibiting high light output is obtained. A semiconductor light emitting device includes a GaP substrate, an active layer located above GaP substrate and including an n-type AlInGaP layer and a p-type AlInGaP layer, and an ELO layer located between GaP substrate and active layer and formed by epitaxial lateral growth. --